SCDS236B-DECEMBER 2006-REVISED APRIL 2009

DUAL SUPPLY, LOW ON-STATE RESISTANCE SPST CMOS ANALOG SWITCHES

FEATURES

- ±1-V to ±6-V Dual-Supply Operation
- Specified ON-State Resistance:
 - 25 Ω Max With ±5-V Supply
 - 35 Ω Max With ±3.3-V Supply
 - 47 Ω Max With ±1.8-V Supply
- Specified Low OFF-Leakage Currents:
 - 5 nA at 25°C
 - 10 nA at 85°C

- Specified Low ON-Leakage Currents:
 - 5 nA at 25°C
 - 10 nA at 85°C
- Low Charge Injection: 13 pC (±5-V Supply)
- Fast Switching Speed:
 - t_{ON} = 85 ns, t_{OFF} = 50 ns (±5-V Supply)
- Break-Before-Make Operation (t_{ON} > t_{OFF})
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2500-V Human-Body Model (A114-F)
 - 1000-V Charged-Device Model (C101-C)
 - 250-V Machine Model (A115-A)

DESCRIPTION/ORDERING INFORMATION

The TS12A4516/TS12A4517 are single pole/single throw (SPST), low-voltage, dual-supply CMOS analog switches, with very low switch ON-state resistance. The TS12A4516 is normally open (NO). The TS12A4517 is normally closed (NC).

These CMOS switches can operate continuously with a dual supplies between ± 1 V and ± 6 V [(2 V < (V₊ – V₋) < 12 V]. Each switch can handle rail-to-rail analog signals. The OFF-leakage current maximum is only 5 nA at 25°C or 10 nA at 85°C.

For pin-compatible parts for use with single supply, see the TS12A4514/TS12A4515.

ORDERING INFORMATION

T _A	PACKAGE	(1)(2)	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	SOIC - D	Reel of 1500	TS12A4516D	YD516
	30IC - D	Reel of 2500	TS12A4516DR	10316
–40°C to 85°C	SOP (SOT-23) – DBV	Reel of 3000	TS12A4516DBVR	9CL_
-40 C to 65 C	SOIC – D		TS12A4517D	YD517
	201C - D	Reel of 2500	TS12A4517DR	10517
	SOP (SOT-23) – DBV	Reel of 3000	TS12A4517DBVR	9CM_

⁽¹⁾ Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

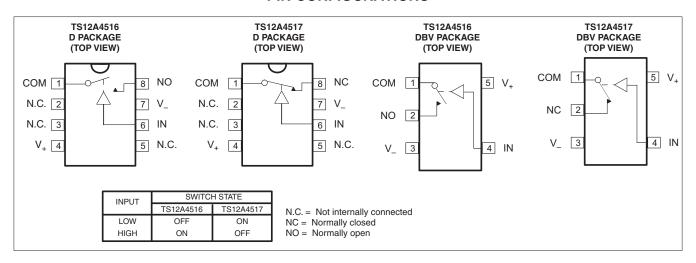


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⁽²⁾ For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.



PIN CONFIGURATIONS



Absolute Minimum and Maximum Ratings (1)(2)

voltages referenced to 0 V

			MIN	MAX	UNIT
V ₊	Supply voltage range	-0.3	13	V	
$V_{NC} V_{NO} V_{COM}$	Analog voltage range ⁽³⁾	V0.3	V ₊ + 0.3	V	
V_{IN}	Logic input range	V0.3	$V_{+} + 0.3$	V	
	Continuous current into any terminal		±20	mA	
	Peak current, NO or COM (pulsed at 1 ms, 1	10% duty cycle)		±30	mA
	ESD per method 3015.7			>2000	V
	Continuous news dissination (T. 70°C)	8-pin SOIC (derate 5.88 mW/°C above 70°C)		471	mW
	Continuous power dissipation (T _A = 70°C)	5-pin SOT23-5 (derate 7.1 mW/°C above 70°C)		571	IIIVV
T _A	Operating temperature range	-40	85	°C	
T _{stg}	Storage temperature range	-65	150	°C	
	Lead temperature (soldering, 10 s)			300	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽³⁾ Voltages exceeding V₊ or GND on any signal terminal are clamped by internal diodes. Limit forward-diode current to maximum current rating.

Electrical Characteristics for ±5-V Supply⁽¹⁾

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $V_{-} = -4.5 \text{ V}$ to -5.5 V, $T_{A} = -40 ^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T _A	MIN TYP ⁽²⁾	MAX	UNIT	
Analog Switch		'		•			
Analog signal range	V_{COM}, V_{NO}, V_{NC}			V_	V ₊	V	
		V ₊ = 4.5 V, V ₋ = -4.5 V,	25°C	12	20		
ON-state resistance	r _{on}	$V_{COM} = 3.5 \text{ V},$ $I_{COM} = 20 \text{ mA}$	Full		25	Ω	
ON-state resistance		$V_{+} = 4.5 \text{ V}, V_{-} = -4.5 \text{ V},$	25°C	1.2	2.5	_	
flatness	r _{on(flat)}	$V_{COM} = -3.5 \text{ V}, 0 \text{ V}, 3.5 \text{ V},$ $I_{COM} = 20 \text{ mA}$	Full		3	Ω	
NO, NC	I _{NO(OFF)} ,	$V_{+} = 5.5 \text{ V}, V_{-} = -5.5 \text{ V},$	25°C		5		
OFF leakage current ⁽³⁾	I _{NC(OFF)}	$V_{COM} = 4.5 \text{ V},$ $V_{NO} \text{ or } V_{NC} = -4.5 \text{ V}$	Full		10	nA	
COM		$V_{+} = 5.5 \text{ V}, V_{-} = -5.5 \text{ V},$	25°C		5	А	
OFF leakage current ⁽³⁾	I _{COM(OFF)}	$V_{COM} = -4.5 \text{ V},$ $V_{NO} \text{ or } V_{NC} = 4.5 \text{ V}$	Full		10	nA	
СОМ		$V_{+} = 5.5 \text{ V}, V_{-} = -5.5 \text{ V},$	25°C		5		
ON leakage current ⁽³⁾	I _{COM(ON)}	$V_{COM} = 5.5 \text{ V},$ $V_{NO} \text{ or } V_{NC} = \text{open}$	Full		10	nA	
Digital Control Input (IN)							
Input logic high	V_{IH}		Full	V ₊ – 1.5		V	
Input logic low	V_{IL}		Full	V_	$V_{+} - 3.5$	V	
Input leakage current	$I_{\mathrm{IH}},I_{\mathrm{IL}}$	$V_{IN} = V_+, 0 V$	Full		0.010	μΑ	
Dynamic							
Turn-on time	t _{ON}	Coo Figure 2	25°C	58	75		
		See Figure 2	Full		85	ns	
Turn-off time	•	Soo Figure 2	25°C	28	45	ns	
rum-on time	t _{OFF}	See Figure 2	Full		50	115	
Charge injection ⁽⁴⁾	Q _C	$C_L = 1 \text{ nF}, V_{NO} = 0 \text{ V},$ $R_S = 0 \Omega$, See Figure 1	25°C	-13		рС	
NO, NC OFF capacitance	$C_{NO(OFF)}, \ C_{NC(OFF)}$	f = 1 MHz, See Figure 4	25°C	5.5		pF	
COM OFF capacitance	C _{COM(OFF)}	f = 1 MHz, See Figure 4	25°C	5.5		pF	
COM ON capacitance	C _{COM(ON)}	f = 1 MHz, See Figure 4	25°C	16		pF	
Digital input capacitance	C_{l}	$V_{IN} = V_+, 0 V$	25°C	1.5		рF	
Bandwidth	BW	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C	464		MHz	
OFF isolation	O _{ISO}	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 1 MHz$	25°C	-83		dB	
Total harmonic distortion	THD	$R_L = 600 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 20 kHz$	25°C	0.07		%	
Supply		'		•			
		., ., .,	25°C		70		
V ₊ supply current	I ₊	$V_{IN} = 0 \text{ V or } V_+$	Full		80	μΑ	
			25°C	-70		μΑ	
V_ supply current	I_	$V_{IN} = 0 V \text{ or } V_+$	Full	-80			

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

⁽²⁾ Typical values are at $T_A = 25$ °C.

⁽³⁾ Leakage parameters are 100% tested at maximum-rated hot operating temperature, and are ensured by correlation at 25°C.

⁽⁴⁾ Specified by design, not production tested



Electrical Characteristics for ±3.3-V Supply⁽¹⁾

 V_+ = 3.0 V to 3.6 V, V_- = -3.0 V to -3.6, T_A = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T _A	MIN	TYP ⁽²⁾	MAX	UNIT	
Analog Switch	1		1	1		Ų.		
Analog signal range	V_{COM}, V_{NO}, V_{NC}			V_		V ₊	V	
		V ₊ = 3.0 V, V ₋ = -3.0 V,	25°C		17	25		
ON-state resistance	r _{on}	$V_{COM} = 3 \text{ V},$ $I_{COM} = 20 \text{ mA}$	Full			35	Ω	
ON-state resistance	r	$V_{COM} = -2 V, 0 V, 2 V,$	25°C		1.5	3	Ω	
flatness	r _{on(flat)}	I _{COM} = 20 mA	Full			4	32	
NO, NC	I _{NO(OFF)} ,	$V_{+} = 3.6 \text{ V}, V_{-} = -3.6 \text{ V},$	25°C			5		
OFF leakage current ⁽³⁾	I _{NC(OFF)}	$V_{COM} = 3 \text{ V},$ $V_{NO} \text{ or } V_{NC} = -3 \text{ V}$	Full			10	nA	
СОМ		$V_{+} = 3.6 \text{ V}, V_{-} = -3.6 \text{ V},$	25°C			5		
OFF leakage current (3)	I _{COM(OFF)}	$V_{COM} = -3 \text{ V},$ $V_{NO} \text{ or } V_{NC} = 3 \text{ V}$	Full			10	nA	
СОМ		$V_{+} = 3.6 \text{ V}, V_{-} = -3.6 \text{ V},$	25°C			5		
ON leakage current ⁽³⁾	I _{COM(ON)}	$V_{COM} = 3.6 \text{ V},$ $V_{NO} \text{ or } V_{NC} = \text{open}$	Full			10	nA	
Digital Control Input (IN)								
Input logic high	V _{IH}		Full	V ₊ – 1.5			V	
Input logic low	V_{IL}		Full	V_		$V_{+} - 3.5$	V	
Input leakage current	I _{IH} , I _{IL}	V _{IN} = V ₊ , 0 V	Full			0.01	μΑ	
Dynamic						<u> </u>		
Turn-on time	t _{ON}	Firms 0	25°C		65	85		
		see Figure 2	Full			95	ns	
Towns of the second		Firm 0	25°C		37	60		
Turn-off time	t _{OFF}	see Figure 2	Full			70	ns	
Charge injection ⁽⁴⁾	Q _C	$C_L = 1 \text{ nF}, V_{NO} = 0 \text{ V},$ $R_S = 0 \Omega$, See Figure 1	25°C		-7.5		рС	
NO, NC OFF capacitance	C _{NO(OFF)} C _{NC(OFF)}	f = 1 MHz, See Figure 4	25°C		5.5		pF	
COM OFF capacitance	C _{COM(OFF)}	f = 1 MHz, See Figure 4	25°C		5.5		pF	
COM ON capacitance	C _{COM(ON)}	f = 1 MHz, See Figure 4	25°C		16		pF	
Digital input capacitance	Cı	V _{IN} = V ₊ , 0 V	25°C		1.5		pF	
Bandwidth	BW	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C		464		MHz	
OFF isolation	O _{ISO}	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C		-83		dB	
Total harmonic distortion	THD	$R_L = 600 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 20 kHz$	25°C		0.10		%	
Supply				•				
M. samakasan		V 0.V == V	25°C			40	μА	
V ₊ supply current	I ₊	$V_{IN} = 0 \text{ V or } V_+$	Full			45		
		V 0.V V	25°C	-40			μΑ	
V_ supply current	I_	$V_{IN} = 0 \text{ V or } V_+$	Full	45				

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

Typical values are at $T_A = 25$ °C.

 ⁽³⁾ Leakage parameters are 100% tested at maximum-rated hot operating temperature, and are ensured by correlation at 25°C.
 (4) Specified by design, not production tested

Electrical Characteristics for ±1.8-V Supply⁽¹⁾

 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $V_{-} = -1.65 \text{ V}$ to -1.95 V, $T_{A} = -40 ^{\circ}\text{C}$ to $85 ^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	T _A	MIN	TYP ⁽²⁾	MAX	UNIT		
Analog Switch									
Analog signal range	V_{COM} , V_{NO} , V_{NC}			V_		V ₊	V		
		V ₊ = 1.65 V, V ₋ = -1.65 V,	25°C		28	40			
ON-state resistance	r _{on}	$V_{COM} = 0 \text{ V},$ $I_{COM} = 20 \text{ mA}$	Full			47	Ω		
ON-state resistance		$V_{+} = 1.65 \text{ V}, V_{-} = -1.65 \text{ V},$	25°C		9	13	0		
flatness	r _{on(flat)}	$V_{COM} = -1.8 \text{ V}, 0 \text{ V}, 1.5 \text{ V},$ $I_{COM} = 20 \text{ mA}$	Full			15	Ω		
NO, NC	I _{NO(OFF),}	$V_{+} = 1.95 \text{ V}, V_{-} = -1.95 \text{ V},$	25°C			5	^		
OFF leakage current ⁽³⁾	I _{NC(OFF)}	$V_{COM} = 1.65 \text{ V},$ $V_{NO} \text{ or } V_{NC} = -1.65 \text{ V}$	Full			10	nA		
СОМ		$V_{+} = 1.95 \text{ V}, V_{-} = -1.95 \text{ V},$	25°C			5			
OFF leakage current ⁽³⁾	I _{COM(OFF)}	$V_{COM} = -1.65 \text{ V},$ $V_{NO} \text{ or } V_{NC} = 1.65 \text{ V}$	Full			10	nA		
СОМ		V ₊ = 1.95 V, V ₋ = -1.95 V,	25°C			5			
ON leakage current ⁽³⁾	I _{COM(ON)}	$V_{COM} = 1.95 \text{ V},$ $V_{NO} \text{ or } V_{NC} = \text{open}$	Full			10	nA		
Digital Control Input (IN)									
Input logic high	V_{IH}		Full	V ₊ – 1.5			V		
Input logic low	V_{IL}		Full	V_		$V_{+} - 3.5$	V		
Input leakage current	$I_{\mathrm{IH}},\ I_{\mathrm{IL}}$	$V_{IN} = V_+, 0 V$	Full			0.01	μΑ		
Dynamic									
Turn-on time (4)	t _{ON}	See Figure 2	25°C		90	120	ns		
		See Figure 2	Full			150	115		
Turn-off time ⁽⁴⁾	t	See Figure 2	25°C		95	150	ns		
Turr on time	t _{OFF}	Occ riguic 2	Full			200	113		
Charge injection ⁽⁴⁾	Q_{C}	C _L = 1 nF, See Figure 1	25°C		-3.5		рC		
NO, NC OFF capacitance	${\sf C_{NO(OFF)}}, \ {\sf C_{NC(OFF)}}$	f = 1 MHz, See Figure 4	25°C		6		pF		
COM OFF capacitance	$C_{\text{COM(OFF)}}$	f = 1 MHz, See Figure 4	25°C		6		pF		
COM ON capacitance	C _{COM(ON)}	f = 1 MHz, See Figure 4	25°C		14.5		pF		
Digital input capacitance	C_{l}	$V_{IN} = V_+, 0 V$	25°C		1.5		pF		
Bandwidth	BW	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 100 kHz$	25°C		464		MHz		
OFF isolation	O _{ISO}	$R_L = 50 \Omega, C_L = 15 pF,$ $V_{NO} = 1 V_{RMS}, f = 1 MHz$	25°C		-83		dB		
Total harmonic distortion	THD	$R_L = 600 \Omega, C_L = 50 pF,$ $V_{NO} = 1 V_{RMS}, f = 20 kHz$	25°C		0.37		%		
Supply									
V ₊ supply current	1	$V_{IN} = 0 \text{ V or } V_+$	25°C			20	μΑ		
v ₊ supply cullellt	I ₊	VIN — U V OI V+	Full			30			
V_ supply current	L	$V_{IN} = 0 \text{ V or } V_+$	25°C	-20			пΔ		
v_ Supply Guilelli	I_	VIN — 0 V 01 V+	Full	-30		7	μΑ		

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.

Typical values are at $T_A = 25$ °C. Leakage parameters are 100% tested at maximum-rated hot operating temperature, and are ensured by correlation at 25°C.

Specified by design, not production tested



PIN DESCRIPTION(1)

	PIN	I NO.				
TS12	TS12A4516 D, P SOT23-5		2A4517	NAME	DESCRIPTION	
D, P			SOT23-5			
1	1	1	1	COM	Common	
2, 3, 5	_	2, 3, 5	_	N.C.	No connect (not internally connected)	
4	5	4	5	V ₊	Positive power supply	
6	4	6	4	IN	Digital control to connect COM to NO or NC	
7	3	7	3	V_	Negative power supply	
8	2	_	-	NO	Normally open	
-	_	8	2	NC	Normally closed	

⁽¹⁾ NO, NC, and COM pins are identical and interchangeable. Any may be considered as an input or an output; signals pass in both directions.

APPLICATION INFORMATION

Power-Supply Considerations

The TS12A4516 and TS12A4517 operate with power-supply voltages from ± 1 V to ± 6 V [(2 V < (V₊ – V₋) < 12 V], but are tested and specified at ± 5 V, ± 3.3 V, and ± 1.8 V supplies. The pin-compatible TS12A4514 and TS12A4515 are recommended for use when only a single supply is desirable.

The TS12A4516 and TS12A4517 construction is typical of most CMOS analog switches, except that they have only two supply pins: V_+ and $V_ V_+$ and V_- drive the internal CMOS switches and set their analog voltage limits. Reverse ESD-protection diodes are internally connected between each analog-signal pin and both V_+ and V_- . One of these diodes conducts if any analog signal exceeds V_+ or V_- .

Virtually all the analog leakage current comes from the ESD diodes to V_+ or V_- . Although the ESD diodes on a given signal pin are identical and, therefore, fairly well balanced, they are reverse biased differently. Each is biased by either V_+ or V_- and the analog signal. This means their leakages will vary as the signal varies. The difference in the two diode leakages to the V_+ and V_- pins constitutes the analog-signal-path leakage current. All analog leakage current flows between each pin and one of the supply terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of the same or opposite polarity.

 V_+ and V_- also power the internal logic and logic-level translators. The logic-level translators convert the logic levels to switched V_+ and V_- signals to drive the analog signal gates.

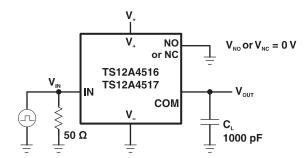
Logic-Level Thresholds

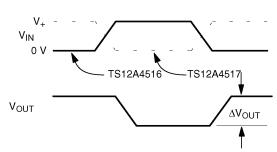
Since these parts have no ground pin, the logic-level threshold is referenced to V_+ . The threshold limits are V_+ –1.5 V and V_+ –3.5 V for V_+ levels between 6 V and 3 V. When V_+ = 2 V, the logic threshold is approximately 0.6 V.

CAUTION:

Do not connect the TS12A4516/TS12A4517 V_{+} to 3 V and then connect the logic-level pins to logic-level signals that operate from 5-V supply. TTL levels can exceed 3 V and violate the absolute maximum ratings, damaging the part and/or external circuits.

Test Circuits/Timing Diagrams





 ΔV_{OUT} is the measured voltage due to charge transfer error Q when the channel turns off.

 $Q = \Delta V_{OUT} \times C_{L}$

Figure 1. Charge Injection



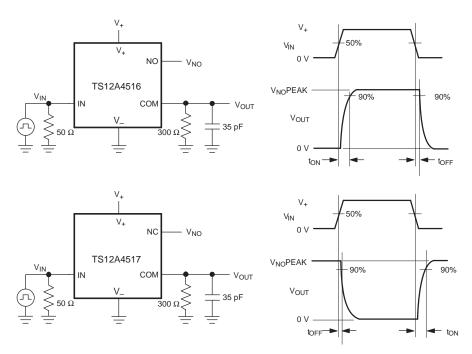


Figure 2. Switching Times

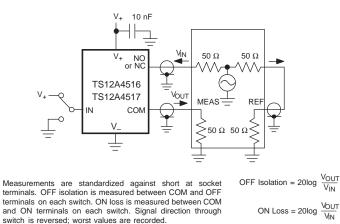


Figure 3. OFF Isolation and ON Loss

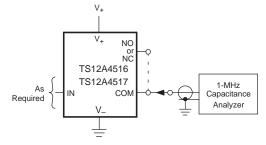


Figure 4. NO, NC, and COM Capacitance





10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	(1)					(2)	(6)	(0)		(40)	
TS12A4516D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YD516	Samples
TS12A4516DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(9CLA, 9CLM)	Samples
TS12A4516DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YD516	Samples
TS12A4517D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YD517	Samples
TS12A4517DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(9CMA, 9CMM)	Samples
TS12A4517DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YD517	Samples
TS12A4517DRG4	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	YD517	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

10-Dec-2020

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

www.ti.com 18-Nov-2020

TAPE AND REEL INFORMATION





_		
		Dimension designed to accommodate the component width
		Dimension designed to accommodate the component length
		Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
Γ	P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS12A4516DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
TS12A4516DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TS12A4517DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

www.ti.com 18-Nov-2020



*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS12A4516DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
TS12A4516DR	SOIC	D	8	2500	853.0	449.0	35.0
TS12A4517DR	SOIC	D	8	2500	853.0	449.0	35.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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